

UNITED STATES PATENT APPLICATION

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FOR

**CURRENT-CONTROLLED POLARIZATION SWITCHING
VERTICAL CAVITY SURFACE EMITTING LASER**

(Atty. Dkt. 098701-0306329; Client Ref. ZIVA-002)

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ACROSS-REFERENCE TO RELATED APPLICATIONS

This application claims the benefit of priority under 35 U.S.C. §119(e) from U.S. Provisional Patent Application No. 60/417,884, filed October 11, 2002 to Husain et al. and entitled "Current-controlled polarization switching VCSEL," which is incorporated herein by
5 reference in its entirety and for all purposes.

This application also claims the benefit of priority under 35 U.S.C. §119(e) from the U.S. Provisional Patent Application No. 60/XXX,XXX (Attorney Docket No. 098701-0306365), filed October 10, 2003 to Krishnamoorthy et al. and entitled "Driver for Polarization-Switching VCSEL and Method of Operation," which is incorporated herein by reference in its entirety and
10 for all purposes.

BACKGROUND OF THE INVENTION

Field of the Invention

The present invention relates generally to solid state lasers, and more particularly relates to the polarization switching of vertical cavity surface emitting lasers, or VCSELs.

Description of the Related Art

Optical interconnections and transceivers are currently being used to provide reliable interconnections between electronic components that can scale in both distance and speed. The VCSEL technology has had a substantial impact on this industry as a low-cost, wafer-scale, and high-speed device that can be directly driven by low-cost silicon circuits. For reasons of
20 manufacturing cost, packaging costs and performance, current-injection (or current-modulation) VCSELs have dominated the low-cost, short reach markets for transceivers in the 1-10 Gigabit per second (Gbit/s) range. However, these conventional current-injection VCSELs are, for numerous reasons, bandwidth limited.

For example, the current-injection VCSELs exhibit RC limits due to charging and
25 discharging of the VCSEL and electrode (i.e., the contacts) capacitances. Electrode capacitance

can be eliminated by suitable design of non-overlapping intra-cavity contacts placed on opposite sides of the cavity to avoid lateral electrode overlap. However, VCSEL intrinsic capacitance (i.e., the active-layer capacitance), to date, cannot be easily reduced. While the intrinsic bandwidth (f_{\max}) of VCSELs, based on their fundamental material properties, can theoretically be in excess of 90 Gigahertz (GHz), the RC limits due to the charging and discharging of the VCSEL and electrode capacitances have limited the operating bandwidth to about 20 GHz for even the fastest conventional VCSELs. Additionally, the conventional current-injection VCSEL experiences detrimental carrier transport effects related to movement and re-distribution of carriers in active region. Further, heating effects caused by current modulation reduces the intrinsic bandwidth (f_{\max}) of a VCSEL. Finally, mode-competition negatively effects the multi-modal VCSELs.

Conventional VCSEL structures also typically have random polarization states. Much work has been done in the art to attempt to understand the dynamics of the polarization behavior of VCSELs. In a typical prior art VCSEL, as the injected current is varied, the polarization state can exhibit hysteresis and noisy behavior. This makes the polarization state of the output light difficult to predict and control. However, it is known that one may “fix” the polarization state of a conventional VCSEL by introducing an asymmetry into the cavity structure through the use of mechanical strain. Mechanisms used to apply the strain in different directions in order to switch the polarization have been proposed. However, due to the need to mechanically alter the stress, these proposed switching mechanisms are inherently slow.

It is also known in the art that by designing a VCSEL with a rectangular aperture, the polarization state of the output light prefers to align along the direction of the longer axis of the rectangular aperture. Further, polarization switching VCSEL designs based on the intersection of such rectangular aperture regions and switching current flow along the corresponding longer axes have been proposed. Aside from even more complex aperture geometries and associated processing complexities, such designs necessitate a more substantial movement and re-distribution of carriers in the active region of the VCSEL, which tends to reduce the maximum rate of switching between the preferred polarization states.

It has also been observed that it is possible to substantially fix the polarization of a square cavity VCSEL by using asymmetric non-overlapping electrodes to preferentially inject current along one lateral axis of the cavity. The proposed structure used a multi-layer Distributed Bragg Reflector (DBR), and one generalized embodiment is shown in Figure 1. As shown in Figure 1, both top and bottom DBR mirrors are used, which makes the fabrication of such a VCSEL with one pair of dual intra-cavity contacts difficult and the fabrication of such a VCSEL with two pairs of dual intra-cavity contacts extremely difficult.

Figure 2 illustrates another generalized example of a prior art VCSEL structure. As shown in Figure 2, the VCSEL structure includes one pair of intra-cavity contacts (i.e. one p-contact 202 and one n-contact 204). A top mirror 206 may be a deposited dielectric for maximum processing flexibility and VCSEL reliability. This contact is in stark contrast to the top DBR mirror used in the device shown in Figure 1. The bottom mirror 208 of the Figure 2 device can be epitaxially grown and is a semiconductor DBR. The n-contact 204 is disposed on the bottom mirror 208. The VCSEL mesa includes the active quantum-well region 210, a current confinement aperture 212, and the remainder of the optical cavity 214. The p-contact 202 is disposed on top of the VCSEL mesa. The dielectric top mirror 206 is placed as the last step of the fabrication process, completing the cavity structure. The pair of contacts 202, 204 are intra-cavity because they bypass the mirror pairs.

Therefore, what is needed is a VCSEL that provides fast switching of the polarization state without the limitations of the conventional art.

SUMMARY OF THE INVENTION

The present invention achieves very fast switching of the polarization-state of the output laser light. The high finesse of the vertical cavity laser enhances small anisotropies in the device, which are caused by injecting current along a uni-axial direction into the aperture and result in the polarization state of the device being fixed orthogonally to the direction of current flow. In an exemplary design intended to achieve polarization switching with approximately equal power outputs in both polarization states and with a high polarization contrast ratio, the aperture typically is small and symmetric, as in, for example, a rectangle. Two orthogonal current paths

are established. The anode and cathode of a first current path are positioned along a first pair of opposite sides of the aperture, while the corresponding anode and cathode of a second, independent current path are positioned along the remaining pair of opposite sides of the aperture.

5 The present invention enables the creation of, along with other aspects, a single-mode, current-injected semiconductor laser with very high-modulation speed (i.e., in excess of 40 Gbit/s and potentially the intrinsic bandwidth (f_{\max}) of the VCSEL) that can be useful in, for example, optical communication, optical imaging and optical sensing applications.

10 Other advantages of various implementations of the present invention include, but are not limited to (nor intended to be limited by):

the ability to decouple the laser turn-on current from the switching mechanism resulting in a low (i.e., near-zero) chirp;

the ability to provide a constant-current, constant electrical power device, thereby reducing the difficulty of thermal dissipation, and packaging;

15 the ability to achieve high-speed and high extinction ratio simultaneously in a VCSEL because bias points are decoupled from the extinction ratio (a feature not available with a conventional current-intensity modulated VCSELs);

the ability to enable link operation in single-ended mode by converting polarization modulation to intensity modulation; or alternatively, to allow link operation naturally in differential mode (if both polarizations are carried to separate receivers); and

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the ability to decouple the aperture size of the VCSEL from its modulation speed.

This offers a more reliable high-speed design because current density can be reduced versus conventional high speed VCSEL due to the fact that peak currents are lower and because larger aperture devices can be used.

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Yet another feature of at least some embodiments of the present invention are that wavelength is naturally stabilized, such that current and temperature do not change as a function of modulation speed, modulation format, and the like.

BRIEF DESCRIPTION OF THE DRAWINGS

These and other advantages, aspects and features of the present invention will become apparent to those ordinarily skilled in the art upon review of the following description of specific embodiments of the invention in conjunction with the accompanying figures, wherein:

5 Figure 1 shows a generalized structure of the conventional VCSEL, wherein an intra-cavity contacted VCSEL uses both bottom and top epitaxially grown DBR mirrors;

Figure 2 shows a second generalized structure of the conventional VCSEL that has an intra-cavity contacted VCSEL with a bottom DBR mirror and a top deposited dielectric mirror;

10 Figures 3A-B show an exemplary arrangement according the present invention with dual pairs of intra-cavity contacts made on a VCSEL with one DBR mirror and one deposited dielectric mirror;

Figure 4 shows an exemplary arrangement according to the present invention with four pairs of intra-cavity contacts made on a VCSEL;

15 Figure 5 shows another exemplary arrangement according to the present invention with four pairs of intra-cavity contacts made on separate neighboring VCSELs;

Figure 6 shows a generalized circuit structure according to an embodiment of the present invention;

Figure 7 shows a first embodiment of the VCSEL driver circuit according to the present invention;

20 Figure 8 shows a second embodiment of the VCSEL driver circuit according to the present invention;

Figure 9 shows a third embodiment of the VCSEL driver circuit according to the present invention; and

25 Figure 10 shows a fourth embodiment of the VCSEL driver circuit according to the present invention.

DETAILED DESCRIPTION OF THE INVENTION

The present invention will now be described in detail with reference to the drawings, which are provided as illustrative examples of the invention so as to enable those skilled in the art to practice the invention. Notably, the figures and examples below are not meant to limit the scope of the present invention. Where certain elements of the present invention can be partially or fully implemented using components known in the art, only those portions of such known components that are necessary for an understanding of the present invention will be described, while detailed descriptions of other portions of such known components will be omitted so as not to obscure the invention. Further, the present invention encompasses present and future known equivalents to the known components referred to herein by way of illustration.

An embodiment of the present invention is shown in Figures 3A-B, which illustrate, respectively, a side elevation view and a perspective view of the invention. As shown, this embodiment of the present invention entails the use of two pairs of orthogonal, lateral-injection, contact electrodes, 302A,B & 304A,B, with a symmetric VCSEL cavity 305 and a dielectric top mirror 306 as a means for polarization switching via current steering. In an exemplary arrangement, the contact pairs 302A,B & 304A,B are arranged on opposite sides of the cavity so as to facilitate uniaxial flow of current across the cavity. The arrows of Figure 3A illustrate this unidirectional current flow between corresponding contacts (i.e., 302A,B in this case). Polarization switching is achieved by changing the direction of this uniaxial current flow.

The use of a relatively thin deposited dielectric mirror 306 allows both a current aperture 312 of predetermined size and the two pairs of intra-cavity contacts, 302A,B & 304A,B, to be accurately positioned with traditional photolithographic processes. The precise thickness of the dielectric mirror 306 is not a critical dimension of the present invention because current does not flow through the dielectric mirror 306, but flows under it and directly into the aperture. Thus, an aspect of the present invention is that the dielectric mirror 306 can be thinner than in the typical design of today. For example, in an 850 nanometer (nm) emitting VCSEL, the dielectric mirror 306 of the present invention can be on the order of 1 micron or less (or even omitted from the design altogether), while in the typical design the mirror (i.e., 206 of Fig. 2) will be at least 3 microns thick. Because the current flow “bypasses” the dielectric mirror 306 and does not have

to flow vertically down (i.e. through) a relatively thick mirror, the direction of flow of current is more controlled (i.e., planar and unidirectional), which leads to the more improved polarization control of the emitted light.

By using this direct current injection into the aperture 312 (which can be much less than 1 micron thick), the present invention enables precise polarization control to be successfully achieved. This procedure avoids the need to define the aperture size by etching a narrow high-aspect ratio mesa or by using proton-implantation through potentially much thicker top-DBR mirror layers, and thus simplifies the fabrication process of the VCSEL. This type of mirror in small dimensions offers greater reliability, including a substantially reduced tendency to delaminate or degrade. The resulting VCSEL has the advantages of high-speed, high extinction ratio, and excellent reliability, attributes that are not simultaneously achievable in conventional current-intensity modulated VCSELs.

Manufacturing the VCSEL of the present invention is performed using typical semiconductor fabrication techniques as are well known in the art. An overview of such fabrication will now be provided. First, a semiconductor DBR 308 is fabricated on a substrate. Such a semiconductor DBR is known in the art. In this example, the semiconductor DBR 308 is approximately circular, with a diameter that can be of any size to support the remaining exemplary features. However, other geometric shapes can be used and the present invention is not intended to be limited to using a circular semiconductor DBR 308. The size of the semiconductor DBR 308 is not critical to the present invention; it could be the entire wafer or it could be selectively deposited in certain areas of the wafer.

Next, an active region (e.g. quantum well region) 310 is centrally disposed on top of the semiconductor DBR 308 using techniques that are known in the art. The active region 310 is also approximately circular and can have a diameter of from about 3 microns to over 20 microns, with typical values being between about 8 and 12 microns. As with the semiconductor DBR 308, other geometric shapes can be used for the active region 310 and are within the scope of the present invention. Part of the active region 310 includes the oxidized current aperture 312 and symmetric VCSEL cavity 305. Also disposed on top of the semiconductor DBR 308 are two n-contacts 302B, 304B, both of which are approximately square pads and about 10 to 50 microns

on a side. However, the shape and size of the pads can vary and depend on the aperture size and capacitance targets, among other variables. The n-contacts 302B, 304B are placed near the outside edge of, and adjacent to, the active region 310 and are spaced approximately 90 degrees apart.

5 On top of the active region 310, a dielectric DBR 306 is centrally disposed and is also approximately circular and about 20 to 100 microns in diameter, with different shapes and sizes possible. Such a dielectric DBR is known in the art. Also disposed on top of the dielectric DBR 306 are two p-contacts 302A, 304A, both of which are approximately square pads and about 10 to 50 microns on a side. However, the shape and size of the pads can vary and depend on the
10 aperture size and capacitance targets, among other variables, as with the n-contacts 302B, 304B. The p-contacts 302A, 304A are placed near the outside edge of, and adjacent to, the dielectric DBR 306. The p-contacts 302A, 304A are approximately 90 degrees apart from one another, and also approximately 180 degrees apart from the corresponding n-contacts 302B, 304B, respectively.

15 It is worth noting again that the sizes and shapes of the parts that make up this embodiment of the VCSEL of the present invention are for example only. It will be readily apparent to those skilled in the art that there are many variations to these sizes and shapes, all of which are intended to be within the scope of the present invention. Further, the materials used for the VCSEL according to the present invention are the ones commonly used to create a
20 VCSEL for any particular emission wavelength. For example, creating an 850 nm VCSEL might require GaAs & AlGaAs, while longer wavelength emissions might use a variety of other materials. The present invention is independent of wavelength, and therefore does not require the use of any particular materials.

In operation, current is supplied (not shown) to the two pair of independent intra-cavity
25 p-contact electrodes and n-contact electrodes, the electrodes being positioned pairs along opposite sides of the aperture in a non-overlapping configuration. The anisotropy resulting from the unidirectional current flow of one electrode pair causes the light output to be polarized perpendicular to the direction of such current flow. Switching of the polarization state of the output light is achieved by using these two orthogonal pairs of non-overlapping intra-cavity

contacted electrodes to switch the direction of current flow in the aperture VCSEL by 90 degrees (i.e., by switching the current flow from one pair to the other pair, the current flow within the VCSEL is switched by +/- 90 degrees, thereby switching the polarization state of the output light).

5 Figure 4 illustrates another embodiment of the present invention that allows a VCSEL to emit in one of multiple linear polarizations. As shown in Figure 4, multiple pairs of electrodes, 402A-405A & 402B-405B, corresponding to multiple pairs of p-n contacts may be placed around the aperture. This enables unidirectional current flow and consequently laser emission in one of multiple linear polarization states. Although four pairs of contacts are illustrated, it will be
10 apparent to those skilled in the art that any number of contact pairs may be fabricated, and such modifications are intended to be within the scope of the present invention.

 Figure 5 illustrates an embodiment according to the present invention that permits simultaneous emission in multiple polarizations using multiple VCSEL cavities that are closely spaced with linear electrodes corresponding to the separate polarization states. As shown in
15 Figure 5, multiple pairs of p-n contacts 502A-505A & 502B-505B are placed around separate, closely spaced current apertures, enabling simultaneous unidirectional current-flow in each cavity between corresponding p-n contacts.

 In another embodiment of the present invention, an exemplary structure maintains near-constant current in the device with minimal resistive differences between the current paths,
20 which mitigates the RC effects and achieves polarization switching at high speeds. This design decouples the operating bias points (and hence optical output power) from the extinction ratio, thereby allowing independent optimization of each. Further, to mitigate thermal-heating effects, exemplary embodiments of the VCSEL structure according to the present invention may be operated at a lower than typical threshold, and well below rollover current. The rollover current
25 depends on the particular VCSEL size; a typical commercial VCSEL may have a threshold of 2 milliamp (mA) and a rollover current of 15 mA. The important point for comparison to aspects of the present invention is that for typical VCSEL current modulation (i.e. modulating the intensity of the output light), the speed of the VCSEL is essentially proportional to the square root of the operating (i.e., bias) current density minus the threshold current density.

As an example of the previous discussion, suppose the typical VCSEL can be operated at a certain speed, X , by using a 3 mA bias, where $I_{\text{bias}} - I_{\text{threshold}} = 1 \text{ mA}$ & $(1)^{1/2} = 1$. Then to double the speed of the VCSEL to $2X$, the bias current would have to be increased to 6 mA, where $I_{\text{bias}} - I_{\text{threshold}} = 4 \text{ mA}$ & $(4)^{1/2} = 2$. Going one step further, to double the speed again to $4X$, would require a bias current to 18 mA, where $I_{\text{bias}} - I_{\text{threshold}} = 16 \text{ mA}$ & $(16)^{1/2} = 4$ (i.e., but 18 mA is beyond the 15 mA rollover current). It can be seen then, that as the speed of the typical VCSEL is increased, the required current quickly grows, heating up the VCSEL. Thus, the output power and speed does not necessarily increase by merely increasing the bias current because of the accompanying detrimental thermal effects. When doing polarization modulation, the speed of the VCSEL is not related to its current density, but rather to how quickly the direction of the polarization of the light can be changed, which is related to the direction of current flow. Therefore, in the present invention, the speed of the VCSEL is decoupled from the bias current or output power of the VCSEL, and the detrimental heating effects are be a barrier to increasing speed. In an exemplary arrangement, one embodiment of a VCSEL device according to the present invention is operated at a threshold of below 1 mA using an oxide-confined aperture.

To mitigate mode-competition effects, one arrangement of the invention provides a single-mode VCSEL with a small aperture (i.e., 5 microns or less). When creating a VCSEL with an aperture having a lateral extent of between less than about 5 microns, laser emissions in a single transverse mode can be achieved. This single-mode VCSEL has advantages in high-speed fiber communication and optical storage applications. However, single-mode lasers typically have lower power emissions, and heat up at lower bias currents than do multimode lasers. Further, the single-mode lasers have unproven reliability. By combining the concepts of the present invention with a typical small-aperture VCSEL, the advantages of single-emissions are achieved without the negative heating effects.

In yet another embodiment of the present invention, the VCSEL is grown on a suitable substrate determined by the desired emission wavelength, for instance: at 850 nm, it is typical that the substrate will be GaAs; at 1.55 microns, materials such as InP could be used; at 1.3 microns, there are a various choices of materials. In this embodiment, the substrate also includes a monolithic tuning network to precisely tune the resistance of the device to approximately 50

Ohms (i.e., 100 Ohms differential). This tuning matches the output impedances of the VCSEL circuits, which has the beneficial effect of minimizing the electrical reflections within the device. This monolithic tuning network can be fabricated adjacent to, or close to, the VCSEL that it will tune. Other fabrication configurations are possible and are well known in the art. The idea is
5 that the tuning network can be part of the same wafer rather than separately fabricated or discretely designed (i.e., designed on board using discrete elements).

From the foregoing, the present invention can be seen to provide a single-mode, current-injected semiconductor laser with high-modulation speeds (i.e., modulation speeds in excess of 40 Gbit/s), which can approach f_{\max} of the VCSEL. The present invention allows link operation
10 in single-ended mode by converting polarization modulation to intensity modulation; alternatively, it allows link operation naturally in differential mode (i.e., if both polarizations are carried to separate receivers). Further, the VCSEL of the present invention can be useful in, for example, optical communication, optical imaging and optical sensing applications.

As discussed, an embodiment of the VCSEL according to the present invention entails
15 the use of two pairs of orthogonal lateral-injection contact electrodes with a single VCSEL cavity as a means for polarization switching via current steering. This design decouples the operating bias points (and hence optical output power) from the extinction ratio, thereby allowing independent optimization of each. In an exemplary arrangement (as previously described in relation to Figures 3A-B), the contact pairs are arranged on opposite sides of the VCSEL cavity
20 so as to allow uniaxial flow of current across the cavity. Polarization switching is achieved by changing the direction of this uniaxial current flow. To mitigate RC effects and to achieve polarization switching at high speeds, an exemplary driver circuit for the VCSEL of the present invention should maintain near-constant current in the device with minimal resistive differences between the current paths.

25 Figure 6 shows a generalized driver circuit arrangement according to an embodiment of the present invention. As shown in Figure 6, a control circuit is used to supply current under the control of a tuning voltage (V_{control}) into the polarization-switching VCSEL. The current is switched between two independent branches (p1-n1 and p2-n2) of the VCSEL using a switching circuit under the control of the input switching voltage (V_{switch}). In order to achieve correct

operation of the disclosed VCSEL, current should flow between each designated pair of electrodes on opposite sides of the cavity and current should not flow between neighboring electrodes. To facilitate this, the driver circuit should break the degeneracy between the two pairs of contact electrodes to prevent forbidden (i.e., stray) currents from flowing. Several
5 specific embodiments of polarization-switching VCSEL driver circuits are now presented to exemplify the driver circuit concepts described.

Figure 7 shows a first VCSEL driver circuit embodiment 500 of the invention. For the purposes of Figure 7, the horizontal polarization emission 100 and the vertical polarization emission 102 are shown separately. The p-contact of the respective orthogonal contact
10 electrodes are attached to separate voltage supplies V_{dd1} 101 and V_{dd2} 103, respectively. Transistors 110 and 112 provide a mirrored adjustable bias current I_{bias1} 111 to p-polarized laser light emission. Transistors 114 and 116 correspondingly provide a mirrored adjustable bias current I_{bias2} 115 to h-polarized emissions. The transistors 104 and 106 represent a differential pair driven by digital inputs IN1 105 and IN2 107 that steer the adjustable modulation current
15 I_{mod} 109 generated by transistors 108 and 110 between the two branches of the circuit. The circuit uses a common ground line 117. During operation of the driver circuit 500, current is steered between the two independent branches of the VCSEL under the control of differential inputs. The separate supply voltages are used to isolate the p-contacts of the VCSEL. The circuit 500 provides independent bias currents for each polarization component of the VCSEL.

Figure 8 shows a second VCSEL driver circuit embodiment 600 of the invention. As
20 shown in Figure 8, a variation to the circuit described in Figure 8 would be to use a common positive supply line V_{dd} 125 with separate negative supply lines V_{ss1} 133 and V_{ss2} 135 connected, respectively, to the n-contacts of the horizontal polarized emission 120 and vertical polarized emission 122. The respective bias currents for each branch of the circuit, I_{bias1} and I_{bias2} , can be
25 generated by a simple voltage controlled current sources 124 and 126, respectively. The transistors 128 and 130 represent a pair driven by digital inputs IN1 and IN2 that steer the adjustable modulation current I_{mod} generated by transistor 132 between the two branches of the circuit. Alternately, I_{bias1} and I_{bias2} could be generated by mirror current sources as in Figure 7.

Other variations of these two driver circuits can be easily imagined by those skilled in the art; such variations are intended to be within the scope of the present invention. For example, in Figure 7, adjustable bias currents I_{bias1} 111 and I_{bias2} 115 can be replaced with a digital-to-analog converter for precise external digital control. Although Figure 7 is illustrated using CMOS transistors, the transistors could easily be replaced with bipolar junction transistors for certain high-speed applications. Additionally, discrete components could be used where integrated circuits have been shown. Further, fixed differential input transistors 104 and 106 could be replaced with a bank of different sized transistors chosen to optimize the current steering speed based on the value of I_{mod} . Corresponding variations for the circuit in Figure 8 could be used.

Figure 9 shows a third VCSEL driver circuit embodiment 700 of the invention. Figure 9 illustrates a driver circuit technique to break the degeneracy of the contacts and achieve proper circuit operation by providing current switching transistors for both the positive and negative supply lines. In this variation of the original circuit shown in Figure 7, pass transistors 146 and 146 are inserted between a common positive supply line V_{dd} and the p-polarized and h-polarized emissions, respectively. Pass transistor 144 serves to enable current to flow in the left branch of the circuit, as shown, when input IN1 is high and IN2 is low, while pass transistor 146 simultaneously stops current flow in the right branch of the circuit. Vice-versa, when IN1 is low and IN2 is high, pass transistor 144 prevents the left-hand side of the circuit from drawing current, whereas pass transistor 146 allows current to flow into the right-hand side. This removes VCSEL contact degeneracy while using a common supply voltage line V_{dd} .

Figure 10 shows a fourth VCSEL driver circuit embodiment 800 of the invention. Figure 10 shows a driver circuit derived from Figure 8, using the technique of Figure 9, above. As shown in Figure 10, pass transistors 180 and 182 are inserted between a common ground line V_{ss} and the p-polarized 164 and h-polarized 166 emissions, respectively. When IN1 is high and IN2 is low, pass transistor 180 shutters on and pass transistor 182 respectively shutters off, enabling current to flow into the p-polarized VCSEL contacts 164 and simultaneously preventing current from flowing into the h-polarized VCSEL contacts 166. Vice-versa, when IN2 is high and IN1 is low, the pass transistors 180 and 182 respectively allow current to flow into the h-polarized VCSEL contacts 166 and prevent current flow into the p-polarized contacts 164. Corresponding

circuit variations for generating the I_{bias} currents are possible for the circuits of Figures 9 and 10 as discussed previously for the circuits of Figures 7 and 8.

Although the present invention has been particularly described with reference to the preferred embodiments thereof, it should be readily apparent to those of ordinary skill in the art that changes and modifications in the form and details thereof may be made without departing from the spirit and scope of the invention. For example, those skilled in the art will understand that variations can be made in the number and arrangement of components and contacts illustrated in the figures. Further, while the VCSEL structure of the exemplary figures is shown to be circular, it should be understood that any geometric shape can be fabricated as part of the present invention. It is intended that the appended claims include such changes and modifications.